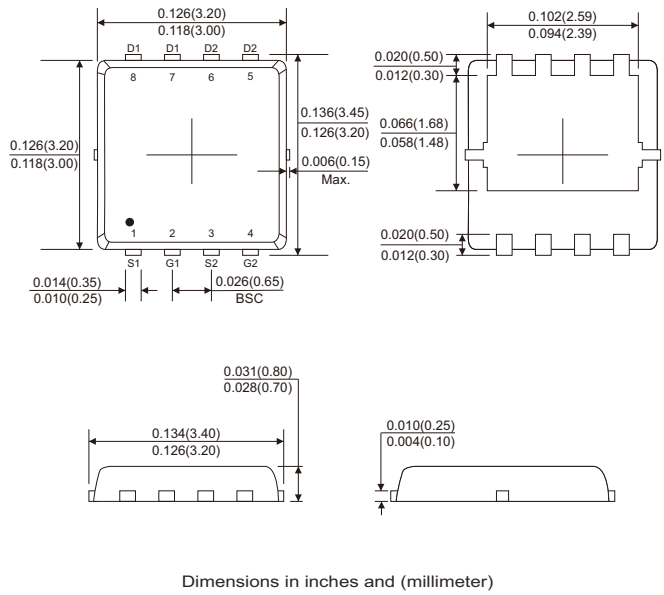
CMS25NN03V8-HF

Dual N-Channel
RoHS Device
Halogen Free

PDFN3.3x3.3(SPR-PAK)



Dimensions in inches and (millimeter)

Features

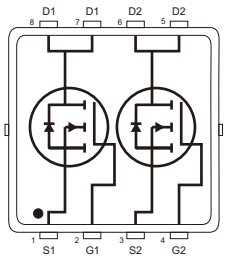
- Advanced high cell density trench technology.
- Super low gate charge.
- Excellent cdv/dt effect decline.
- Green device available.
- 100% EAS guaranteed.

Mechanical data

- Case: PDFN3.3x3.3/SPR-PAK standard package, molded plastic.

Circuit diagram

- G : Gate
- S : Source
- D : Drain



Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	±20	V
Continuous drain current (Note 1, 4)	I_D @ T_C = 25°C		25	A
Continuous drain current (Note 1)	I_D @ T_C = 100°C		16	
Pulsed drain current (Note 1, 2)		I_{DM}	50	A
Total power dissipation (Note 4)	P_D @ T_C = 25°C		20.8	W
	P_D @ T_A = 25°C		1.7	
Single pulse avalanche energy, L=0.1mH (Note 3)		E_{AS}	22	mJ
Single pulse avalanche current, L=0.1mH (Note 3)		I_{AS}	21	A
Operating junction temperature range		T_J	-55 to +150	°C
Storage temperature range		T_{STG}	-55 to +150	°C
Thermal resistance junction-ambient (Note 1)	Steady state	$R_{\theta JA}$	75	°C/W
Thermal resistance junction-case (Note 1)	Steady state	$R_{\theta JC}$	6	°C/W

Electrical Characteristics (at T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA	30			V
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.8	2.5	
Forward transconductance	g_{fs}	V_{DS} = 5V, I_D = 10A		4.5		S
Gate-source leakage current	I_{GSS}	V_{GS} = ±20V			±100	nA
Drain-source leakage current (Tj=25°C)	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V			1	μA
Drain-source leakage current (Tj=55°C)		V_{DS} = 24V, V_{GS} = 0V			5	
Static drain-source on-resistance (Note 2)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 10A			20	mΩ
		V_{GS} = 4.5V, I_D = 5A			30	
Total gate charge (Note 2)	Q_g	I_D = 10A, V_{DS} = 20V, V_{GS} = 4.5V		7.2		nC
Gate-source charge	Q_{gs}			1.4		
Gate-drain ("miller") charge	Q_{gd}			2.2		
Turn-on delay time (Note 2)	$t_{d(on)}$	V_{DS} = 12V, V_{GS} = 10V I_D = 5A, R_G = 3.3Ω		4.1		nS
Rise time	t_r			9.8		
Turn-off delay time	$t_{d(off)}$			15.5		
Fall time	t_f			6.0		
Input capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		572		pF
Output capacitance	C_{oss}			81		
Reverse transfer capacitance	C_{rss}			65		
Gate resistance	R_g	f = 1MHz		2.5		Ω
Source-drain diode						
Diode forward voltage (Note 2)	V_{SD}	I_S = 10A, V_{GS} = 0V, T_J=25°C			1.2	V
Continuous source current (Note 1,6)	I_S	V_G = V_D = 0V, Force current			25	A
Pulsed source current (Note 2,6)	I_{SM}				50	A
Guaranteed avalanche characteristics						
Single pulse avalanche energy (Note 5)	EAS	V_{DD} = 25V, L=0.1mH, I_{AS} = 10A	5			mJ

Notes: 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2 oz copper.
2. The data tested by pulsed, pulse width ≤300μs, duty cycle ≤ 2%.
3. The EAS data shows max. rating. The test condition is VDD=25V, VGS=10V, L=0.1mH, IAS=21A.
4. The power dissipation is limited by 150°C junction temperature.
5. The min. value is 100% EAS tested guarantee.
6. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

Rating and Characteristic Curves (CMS25NN03V8-HF)

Fig.1 - Typical Output Characteristics

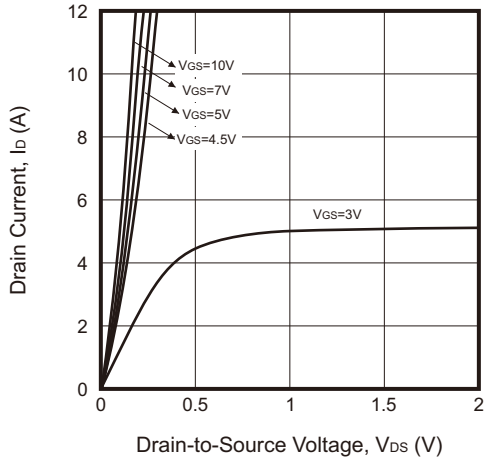


Fig.2 - On-Resistance vs. G-S Voltage

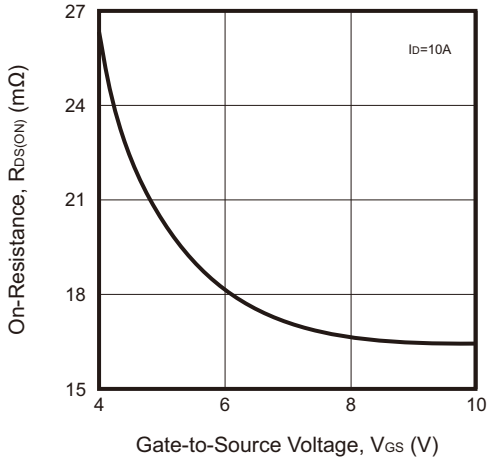


Fig.3 - Normalized $V_{GS(th)}$ vs. T_J

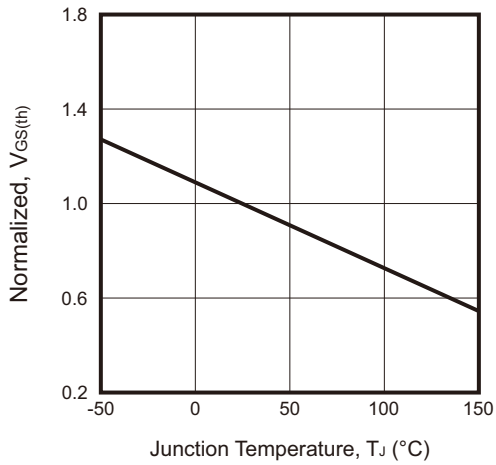


Fig.4 - Normalized $R_{DS(ON)}$ vs. T_J

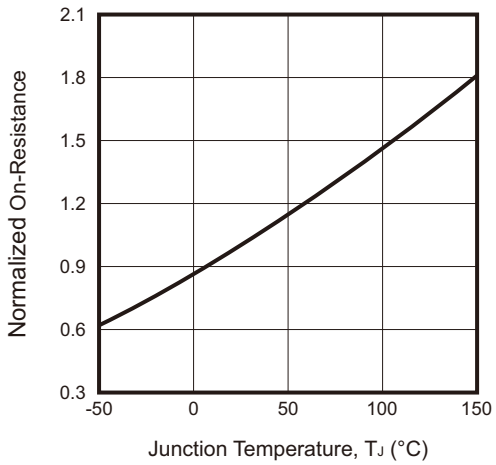


Fig.5 - Safe Operating Area

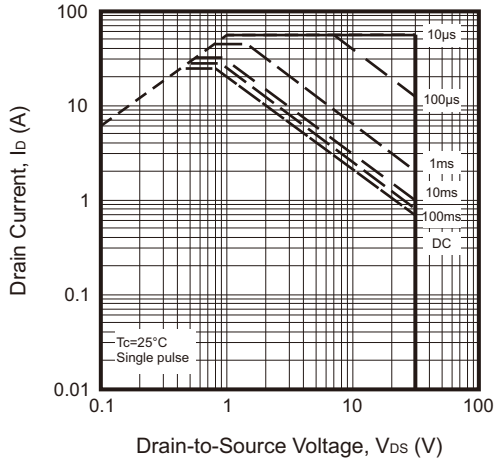
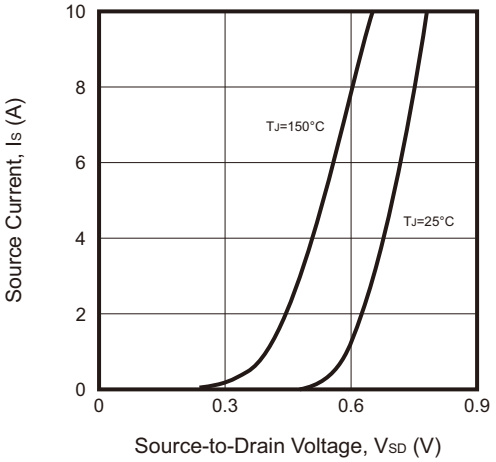


Fig.6 - Forward Characteristics of Reverse



Company reserves the right to improve product design , functions and reliability without notice.

Rating and Characteristic Curves (CMS25NN03V8-HF)

Fig.7 - Gate Charge Characteristics

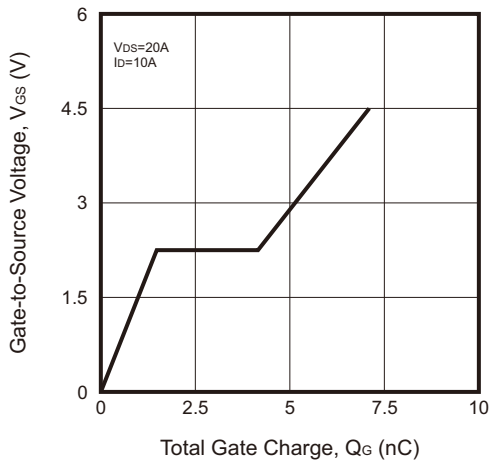
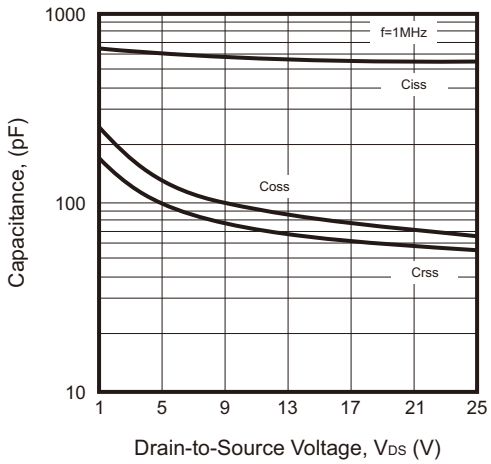
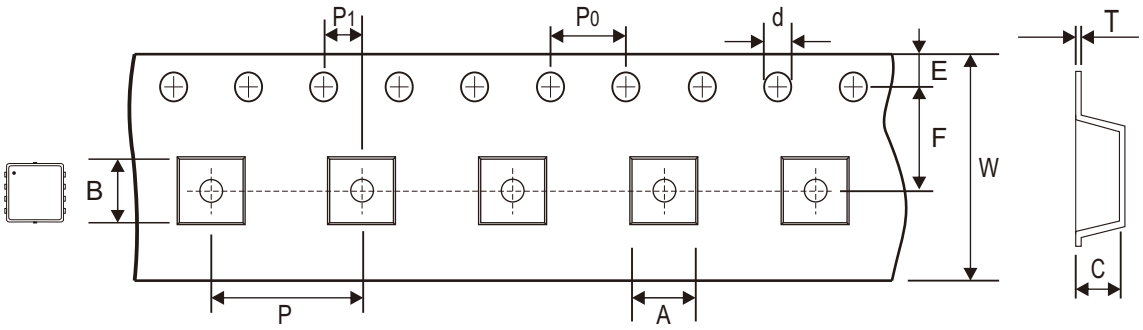
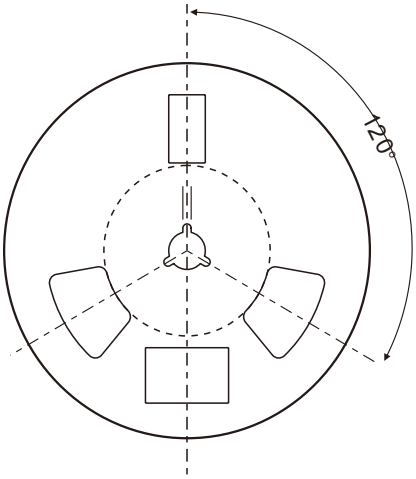


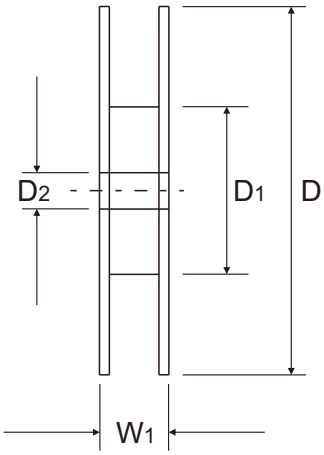
Fig.8 - Capacitance Characteristics

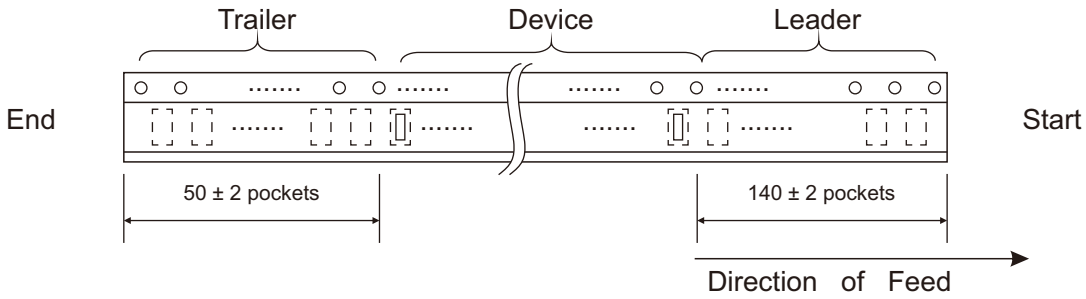


Reel Taping Specification







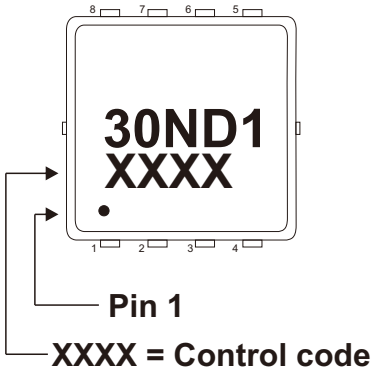


	SYMBOL	A	B	C	d	D	D_1	D_2
SPR-PAK	(mm)	3.55 ± 0.10	3.55 ± 0.10	1.10 + 0.10 - 0.05	1.50 + 0.10 - 0.00	330.00 ± 1.00	178.00 + 0.00 - 2.00	13.00 min.
	(inch)	0.140 ± 0.004	0.140 ± 0.004	0.043 + 0.004 - 0.002	0.059 + 0.004 - 0.000	12.992 ± 0.039	7.008 + 0.000 - 0.079	0.512 min.

	SYMBOL	E	F	P	P_0	P_1	T	W	W_1
SPR-PAK	(mm)	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.30 ± 0.05	12.00 + 0.30 - 0.10	18.40 ref.
	(inch)	0.069 ± 0.004	0.217 ± 0.002	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.012 ± 0.002	0.472 + 0.012 - 0.004	0.724 ref.

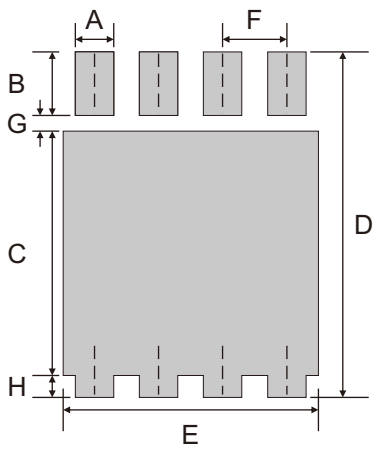
Marking Code

Part Number	Marking Code
CMS25NN03V8-HF	30ND1



Suggested PAD Layout

SIZE	SPR-PAK (PDFN3.3x3.3)	
	(mm)	(inch)
A	0.40	0.016
B	0.60	0.024
C	2.35	0.093
D	3.55	0.140
E	2.80	0.110
F	0.65	0.026
G	0.35	0.014
H	0.25	0.010



Note: 1. The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SPR-PAK (PDFN3.3x3.3)	3000	13